

CLAIMS

1. A semiconductor device comprising:
an active device provided in a semiconductor substrate facing
its principal plane, and
5 a contact electrode provided outside of the semiconductor
substrate conducting with the active device,
wherein a marginal corner of conducting portion of the active
device and the contact electrode is formed with a curved line or with
an obtuse angle.
- 10 2. A semiconductor device of claim 1,
wherein a plurality of active devices are discretely arranged
in the semiconductor substrate, and each active device has a conducting
portion to a contact electrode, and
15 a corner portion of a conducting portion of an active device
positioned at the end and at opposite side to another active device
is formed with a curved line or with an obtuse angle.
- 20 3. A semiconductor device comprising:
an active device provided in a semiconductor substrate facing
its principal plane, and
a contact electrode provided outside of the semiconductor
substrate conducting with the active device,
wherein the shape of conducting portion of the active device
25 and the contact electrode is formed in a broader width in an end portion
than in the central portion.
4. A semiconductor device of claim 3,

wherein a plurality of active devices are discretely arranged in the semiconductor substrate, and each active device has a conducting portion to a contact electrode, and

an end portion of a conducting portion of an active device
5 positioned at an end and at opposite side of another active device is formed broader than the central portion of the conducting portion.

5. A semiconductor device comprising:

an active device provided in a semiconductor substrate facing
10 its principal plane, and

a contact electrode provided outside of the semiconductor substrate conducting with the active device,

wherein impurity concentration is lower at an end portion of conducting portion of the active device and the contact electrode than
15 in the central portion of it.

6. A semiconductor device of claim 5,

wherein a plurality of active devices are discretely arranged in the semiconductor substrate, and each active device has a conducting
20 portion to a contact electrode, and

an end portion of a conducting portion of an active device positioned at an end and at opposite side of another active device is lower in impurity concentration than the central portion of the conducting portion.